

Expertise Applied Answers Delivered

PolyZen Polymer Enhanced Zener Diode Micro-Assemblies

PRODUCT: ZEN098V230A16LS

DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 1 OF 8

Specification Status: Released



GENERAL DESCRIPTION

Littefuse PolyZen devices are polymer-enhanced, precision Zener diode micro-assemblies. They offer resettable protection against multi-Watt fault events and spare the need for large heavy heat sinks.

A unique feature of the PolyZen micro-assembly is that the Zener diode is thermally coupled to a resistively non-linear, polymer PTC (Positive Temperature

Coefficient) layer. This PTC layer is fully integrated into the device, and is electrically in series between V_{IN} and the diode clamped V_{OUT} .

This polymer PTC layer responds to either extended diode heating or overcurrent events by transitioning from a low to high resistance state, also known as "tripping". A tripped PTC will limit current and generate voltage drop. It helps to protect both the Zener diode and the follow-on electronics and effectively increases the diode's power handling capability.

The Zener diode used for voltage clamping in the PolyZen micro-assembly was selected due to its relatively flat voltage vs current response. This helps improve output voltage clamping, even when input voltage is high and diode current is large.

The polymer-enhanced Zener diode helps protect sensitive portable electronics from damage caused by inductive voltage spikes, voltage transients, incorrect power supplies, and reverse bias conditions. The PolyZen ZEN098V230A16LS devices are particularly useful for portable electronics and other low-power DC devices.

TYPICAL APPLICATION BLOCK DIAGRAM

BENEFITS

- Stable Zener diode helps shield downstream electronics from overvoltage and reverse bias
- Trip events shut out overvoltage and reverse bias sources
- Analog nature of trip events minimizes
 upstream inductive spikes
- Minimal power dissipation requirements
- Single component placement

FEATURES

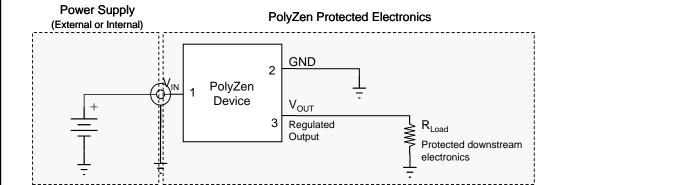
- Overvoltage transient suppression
- Stable Vz vs fault current
- Time delayed, overvoltage trip
- Time delayed, reverse bias trip
- Multi-Watt power handling capability
- Integrated device construction
- RoHS Compliant and Halogen Free

TARGET APPLICATIONS

- DC power port protection in portable electronics
- DC power port protection for systems
 using

barrel jacks for power input

- Internal overvoltage & transient suppression
- DC output voltage regulation



© 2016 Littelfuse, Inc. Specifications are subject to change without notice. Revised July 26, 2016



Pad Dimensions

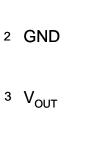
PRODUCT: ZEN098V230A16LS

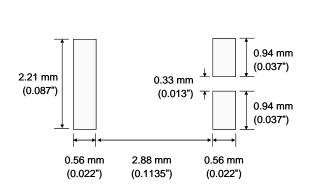
DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 2 OF 8

CONFIGURATION INFORMATION

Pin Configuration (Top View)

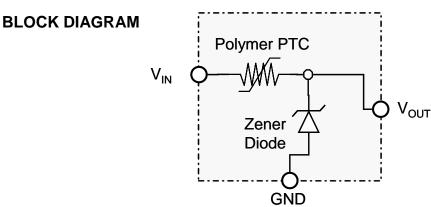






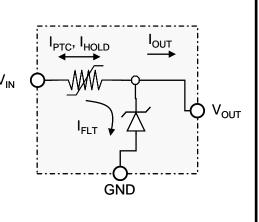
PIN DESCRIPTION

Pin Number	Pin Name	Pin Function
1	Vin	V _{IN} . Protected input to Zener diode.
2	GND	GND
3	Vout	Vour. Zener regulated voltage output



DEFINITION of TERMS

Current flowing through the PTC portion of the	
circuit	
RMS fault current flowing through the diode	1
Current flowing out the VOUT pin of the device	
A condition where the PTC transitions to a high	
resistance state, thereby significantly limiting IPTC	
and related currents.	
Time the PTC portion of the device remains in a	
high resistance state.	
	Current flowing out the V_{OUT} pin of the device A condition where the PTC transitions to a high resistance state, thereby significantly limiting I _{PTC} and related currents. Time the PTC portion of the device remains in a





PRODUCT: ZEN098V230A16LS

DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 3 OF 8

GENERAL SPECIFICATIONS

Operating Temperature -4 Storage Temperature -4

-40° to +85°C -40° to +85°C

ELECTRICAL CHARACTERISTICS^{1-3, 11} (Typical unless otherwise specified)

Vz ⁴ (V)		14	I _{HOLD} ⁵	Leakage Current		D T	D 7	V _{Int} Max ⁸ (V)		I _{FLT} Max ⁹		Tripped Power Dissipation ¹⁰ Max		
Min	Тур	Max	(A)	[®] 20⁰C (A)	Test Voltage	Max Current (mA)	R Typ ⁶ (Ohms)	R _{1Max} ⁷ (Ohms)	V _{⊪ĭ} Max (V)	Test Current (A)	I _{FLT} Max (A)	Test Voltage (V)	Value (W)	Test Voltage (V)
9.6	9.8	10.0	0.1	2.3	9.5	5.0	0.04	0.06	16V	5A	+3.5 -40	+16 -12	1.0	16

Note 1: Electrical characteristics determined at 25°C unless otherwise specified.

Note 2: This device is intended for limited fault protection. Repeated trip events or extended trip endurance can degrade the device and may affect performance to specifications. Performance impact will depend on multiple factors including, but not limited to, voltage, trip current, trip duration, trip cycles, and circuit design. For details or ratings specific to your application contact, Littlefuse Circuit Protection Division directly.

Note 3: Specifications developed using 1.0 ounce 0.045" wide copper traces on dedicated FR4 test boards. Performance in your application may vary.

Note 4: I_{zt} is the current at which V_z is measured ($V_z = V_{OUT}$). Additional V_z values are available on request.

Note 5: I_{HOLD}: Maximum steady state I_{PTC} (current entering or exiting the V_{IN} pin of the device) that will not generate a trip event at the specified temperature. Specification assumes I_{FLT} (current flowing through the Zener diode) is sufficiently low so as to prevent the diode from acting as a heat source. Testing is conducted with an "open" Zener.

Note 6: R Typ: Resistance between VIN and VOUT pins during normal operation at room temperature.

- Note 7: R_{1Max}: The maximum resistance between V_{IN} and V_{OUT} pins at room temperature, one hour after 1st trip or after reflow soldering.
- Note 8: VINT Max: VINT Max relates to the voltage across the PPTC portion of the PolyZen device (VIN-VOUT). VINT Max is defined as the voltage (VIN-VOUT) at which typical qualification devices (98% devices, 95% confidence) survived at least 100 trip cycles and 24 hours trip endurance at the specified voltage (VIN-VOUT) and current (IPTC). VINT Max testing is conducted using a "shorted" load (VOUT = 0 V). VINT Max is a survivability rating, not a performance rating.
- Note 9: I_{FLT} Max: I_{FLT} Max relates to the steady state current flowing through the diode portion of the PolyZen device in a fault condition, prior to a trip event. I_{FLT} Max is defined as the current at which typical qualification devices (12 parts per lot from 3 lots) survived 100 test cycles. RMS fault current above I_{FLT} Max may permanently damage the diode portion of the PolyZen device. Testing is conducted with <u>NO</u> load connected to V_{OUT}, such that I_{OUT} = 0. "Test voltage" is defined as the voltage between V_{IN} to GND and includes the PolyZen Diode drop. Specification is dependent on the direction of current flow through the diode. I_{FLT} Max is a survivability rating, not a performance rating.

Note 10: The power dissipated by the device when in the "tripped" state, as measured on Littelfuse test boards (see note 3). Note 11: Specifications based on limited qualification data and subject to change.

			Min	Typical	Max
MECHANICAL DIMENSIONS	Length	L	3.85 mm (0.152")	4 mm (0.16")	4.15 mm (0.163")
	Width	W	3.85 mm (0.152")	4 mm (0.16")	4.15 mm (0.163")
	Height	н	1.4mm (0.055")	1.7 mm (0.067")	2.0 mm (0.081")
	Length Diode	Ld	-	3.0 mm (0.118")	-
	Height Diode	Hd	-	1.0 mm (0.039")	-
	Offset	O1	-	0.6 mm (0.024")	-
*_ L	Offset	O2	-	0.7 mm (0.028")	-

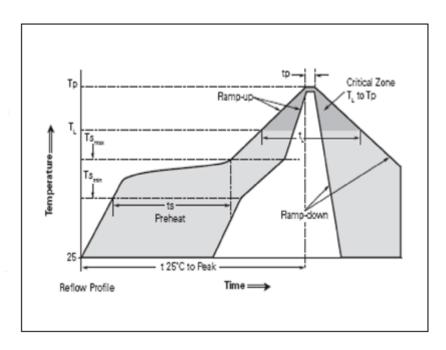


PRODUCT: ZEN098V230A16LS

DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 4 OF 8

SOLDER REFLOW RECOMMENDATIONS:

Classification Reflow Profiles							
Profile Feature	Pb-Free Assembly						
Average Ramp-Up Rate (Tsmax to Tp)	3 °C/second max.						
Preheat							
Temperature Min (Tsmin)	150 °C						
Temperature Max (Tsmax)	200 °C						
• Time (tsmin to tsmax)	60-180 seconds						
Time maintained above:							
Temperature (TL)	217 °C						
• Time (tL)	60-150 seconds						
Peak/Classification Temperature							
(Тр)	260 °C						
Time within 5 °C of actual Peak							
Temperature (tp)	20-40 seconds						
Ramp-Down Rate	6 °C/second max.						
Time 25 °C to Peak Temperature	8 minutes max.						

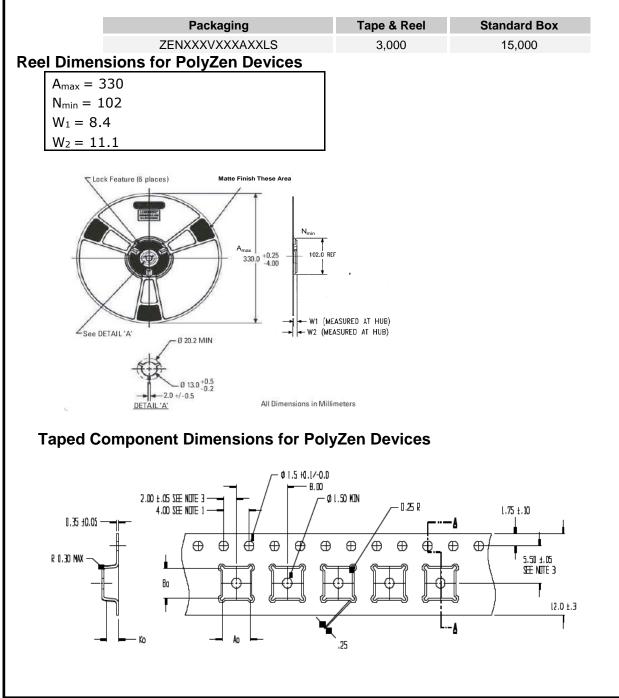




PRODUCT: ZEN098V230A16LS

DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 5 OF 8

PACKAGING





Expertise Applied Answers Delivered

PolyZen Polymer Enhanced Zener Diode Micro-Assemblies

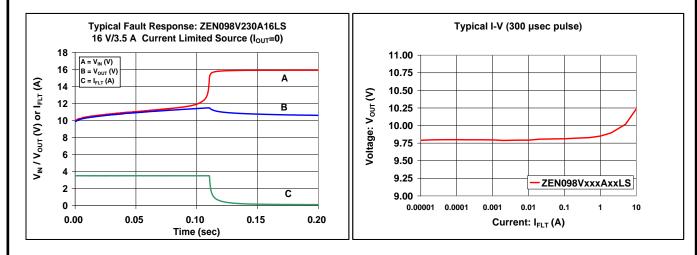
PRODUCT: ZEN098V230A16LS

DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 6 OF 8

NOTES:

- Aa = 4.35 l, 10 SPROEKET HOLE PITCH CLMULATIVE TOLERANCE ±0.2
- Bo = 4.35 2. CAMBER IN COMPLIANCE VITH EIA 481
- Ko = 2.30 3. POCKET POSITION RELATIVE TO SPROCKET HOLE MEASURED AS TRUE POSITION OF POCKET, NOT POCKET HOLE

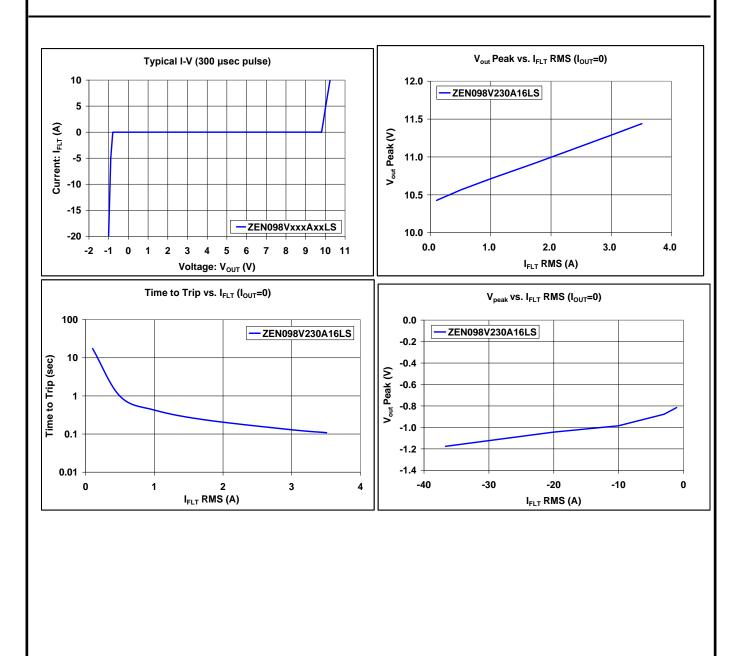
TYPICAL CHARACTERISTICS





PRODUCT: ZEN098V230A16LS

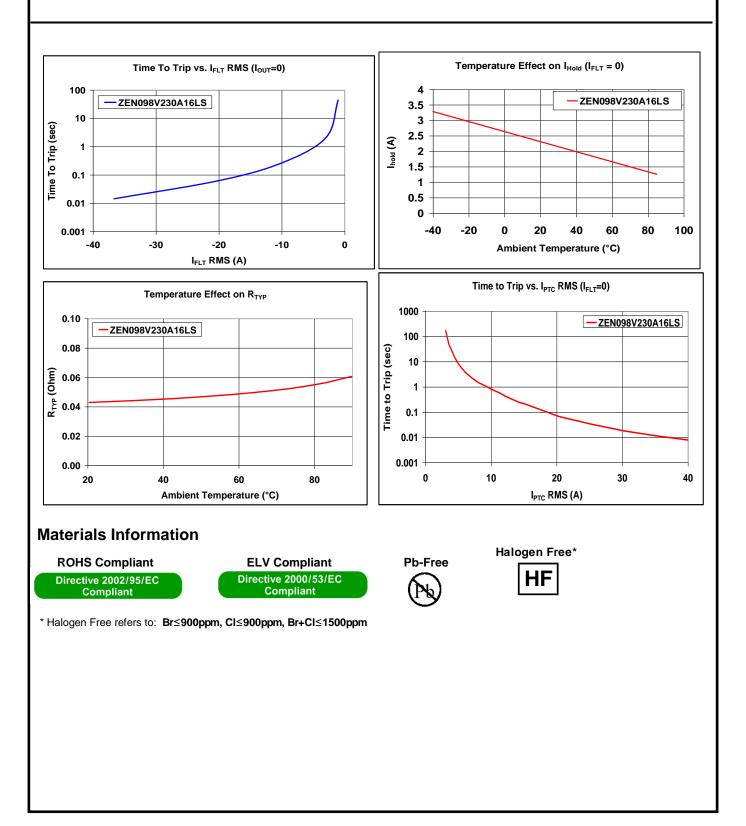
DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 7 OF 8





PRODUCT: ZEN098V230A16LS

DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 8 OF 8





PRODUCT: ZEN098V230A16LS

DOCUMENT: SCD27861 REV LETTER: B REV DATE: JULY 26, 2016 PAGE NO.: 9 OF 8

Littelfuse products are not designed for, and shall not be used for, any purpose (including, without limitation, automotive, military, aerospace, medical, life-saving, life-sustaining or nuclear facility applications, devices intended for surgical implant into the body, or any other application in which the failure or lack of desired operation of the product may result in personal injury, death, or property damage) other than those expressly set forth in applicable Littelfuse product documentation. Warranties granted by Littelfuse shall be deemed void for products used for any purpose not expressly set forth in applicable Littelfuse documentation. Littelfuse shall not be liable for any claims or damages arising out of products used in applications not expressly intended by Littelfuse as set forth in applicable Littelfuse documentation. The sale and use of Littelfuse products is subject to Littelfuse Terms and Conditions of Sale, unless otherwise agreed by Littelfuse.